AMENDMENT UNDER 37 C.F.R. § 1.111 Attorney Docket No.: Q80719

Application No.: 10/591,076

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the

application:

LISTING OF CLAIMS:

1. (currently amended): A compound semiconductor light-emitting device

comprising: a substrate having major an upper surface; and a device side surface; and having a

light-emitting layer provided on the major upper surface of said substrate, wherein at least a part

of a substrate portion of the device side surface has longitudinal-recessed portions inwardly

extended in a side direction of the device perpendicular to the upper surface of the substrate, and

the recessed portions have a semi-circular shape in cross section parallel to the upper surface of

the substrate, and

wherein the depth of the recessed portion is a radius of the semi-circular shape in a

direction parallel to the upper surface of the substrate, and the height of the recessed portion is at

least 20 µm in the side direction of the device perpendicular to the upper surface of the surface of

the substrate, and

wherein a distance of 4 to 40 µm is maintained between the adjacent recessed portions.

2. (original): A light-emitting device according to claim 1, wherein at least a part of

a compound semiconductor portion of the device side surface has recessed portions in a side

direction of the device.

3. (original): A light-emitting device according to claim 1, wherein the light-

emitting layer comprises an n-type or p-type compound semiconductor and is of the pn junction

type.

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4. (original): A light-emitting device according to claim 1, wherein the substrate is selected from the group consisting of a sapphire, a SiC and a III-V Group compound semiconductor single crystal.

- 5. (canceled).
- 6. (original): A light-emitting device according to claim 1, wherein individual ones of the recessed portions have a depth of 0.5 to 10 μ m and a width of 1 to 20 μ m.
- 7. (original): A light-emitting device according to claim 1, wherein the compound semiconductor light-emitting device is of the flip-chip type.
 - 8-17. (canceled).
- 18. (original): A lamp comprising a compound semiconductor light-emitting device of claim 1.
 - 19. (original): A source of light comprising a lamp of claim 18.